

SMD Switching Diode

COMCHIP
SMD Diodes Specialist

CDSFR4148(RoHs Device)

High Speed



Features

Designed for mounting on small surface.

Extremely thin/leadless package.

High mounting capability, strong surge withstand, high reliability.

Use in sensitive electronics protection against voltage transients induced by inductive load switching and lighting on ICs, MOSFET, signal lines of sensor units for consumer, computer, industrial, automotive and telecommunication.

Mechanical data

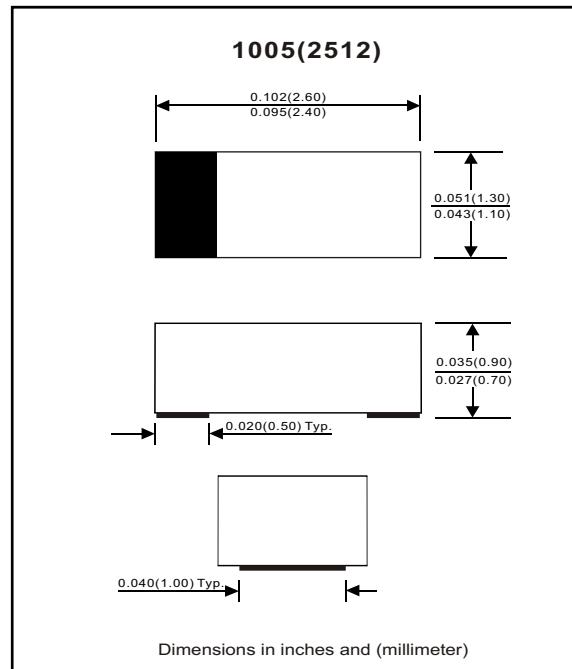
Case: 1005(2512) standard package, molded plastic.

Terminals: Gold plated, solderable per MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.006 gram(approx.).



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V _{RRM}			100	V
Reverse voltage		V _R			75	V
Average forward current		I _o			150	mA
Forward current,surge peak	T _P = 1uS T _P = 1mS	I _{FSM}		4 1		A
Repetitive peak forward current		I _{FRM}			300	mA
Power Dissipation		P _D			350	mW
Storage temperature		T _{TG}	-40		+125	°C
Junction temperature		T _j			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 50 mA DC	V _F			1.0	V
Reverse current	V _R = 20 V V _R = 75 V	I _R			25 2.5	nA uA
Capacitance between terminals	f = 1 MHz, and 0VDC reverse voltage	C _T			4	pF
Reverse recovery time	I _F = I _R = 10 mA, R _L = 100 ohms, I _{rr} = 1mA	T _{rr}			4	nS

RATING AND CHARACTERISTIC CURVES (CDSFR4148)

Fig. 1 - Forward characteristics

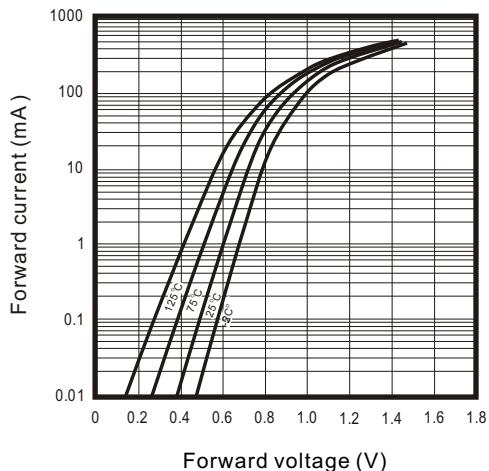


Fig. 2 - Reverse characteristics

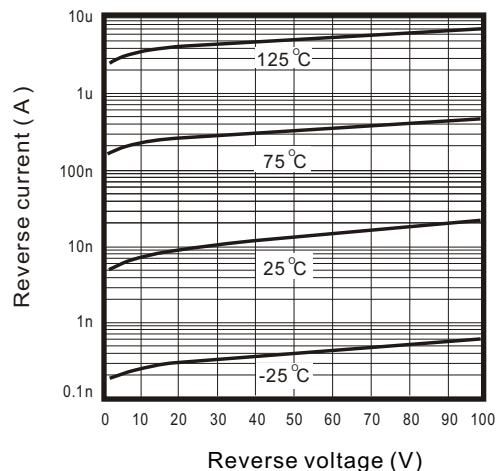


Fig. 3 - Capacitance between terminals characteristics

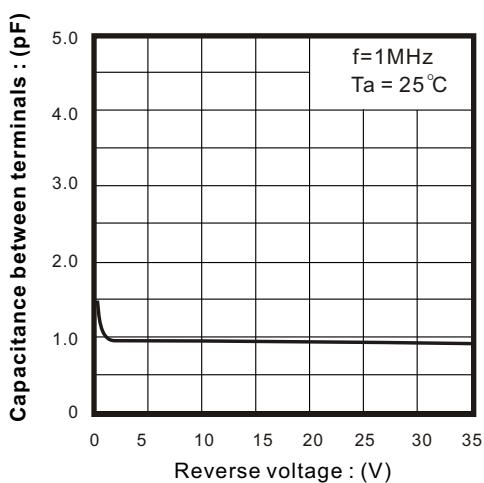


Fig. 4 - Current derating curve

